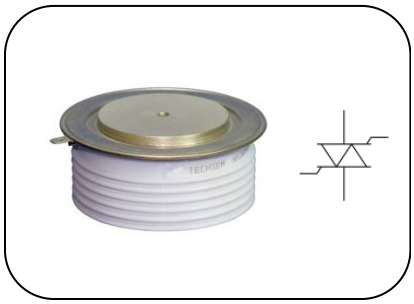


Features：

- International standard cases
- Hermetic metal cases with ceramic insulators
- Capsule packages for double sided cooling

Typical Applications

- High power industrial and power transmission
- DC and AC motor control
- AC controllers

Part No. H50KSR-KS50dT

$I_{T(AV)}$	350A		
V_{DRM},V_{RRM}	5600V	6000V	6500V

SYMBOL	CHARACTERISTIC	TEST CONDITIONS		T_j(°C)	VALUE			UNIT
					Min	Type	Max	
$I_{T(AV)}$	Mean on-state current	180° half sine wave 50Hz Double side cooled	T_C=70°C	125			350	A
$I_{T(RMS)F}$	RMS current(sine wave)	Sine wave 50Hz Double side cooled					770	A
V_{DRM}	Repetitive peak reverse voltage	tp=10ms		125	5600		6500	V
I_{DRM}	Repetitive peak current	at V_{DRM}		125			200	mA
I_{TSM}	Surge on-state current	10ms half sine wave V_R=0.6V_{RRM}		125			4.5	kA
I^2t	I^2t for fusing coordination						101	10^3A^2s
V_{TO}	Threshold voltage			125			1.25	V
r_T	On-state slope resistance						2.20	mΩ
V_{TM}	Peak on-state voltage	I_{TM}=1000A, F=24kN		25			3.50	V
dv/dt	Critical rate of rise of off-state voltage	V_{DM}=0.67V_{DRM}		125			200	V/μs
di/dt	Critical rate of rise of on-state current	V_{DM}= 67%V_{DRM} Gate pulse t_r ≤0.5μs I_{GM}=1.5A Repetitive		125			100	A/μs
I_{GT}	Gate trigger current	V_A=12V, I_A=1A		25	40		350	mA
V_{GT}	Gate trigger voltage				0.8		3.5	V
I_H	Holding current				20		400	mA
I_L	Latching current						500	mA
V_{GD}	Non-trigger gate voltage	V_{DM}=67%V_{DRM}		125			0.3	V
$R_{th(j-c)}$	Thermal resistance Junction to case	Double side cooled Clamping force 24kN					0.045	°C /W
$R_{th(c-h)}$	Thermal resistance case to heat sink						0.008	
F_m	Mounting force				19		26	kN
T_{vj}	Junction temperature				-40		125	°C
T_{stg}	Stored temperature				-40		140	°C
W_t	Weight					440		g
Outline	KS50dT							

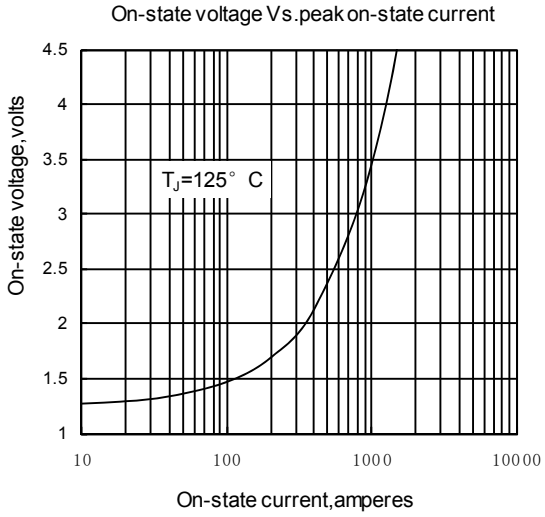


Fig1

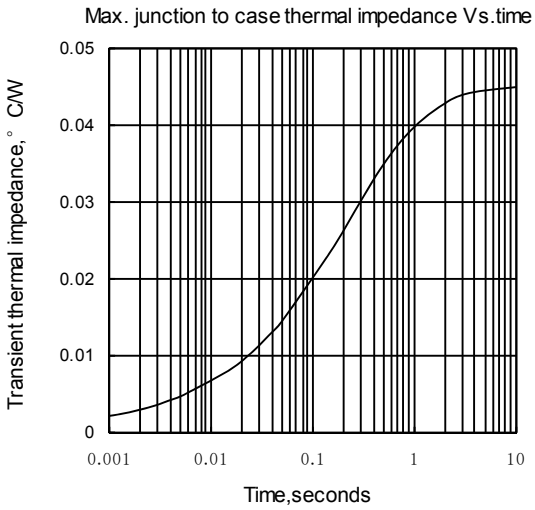


Fig2

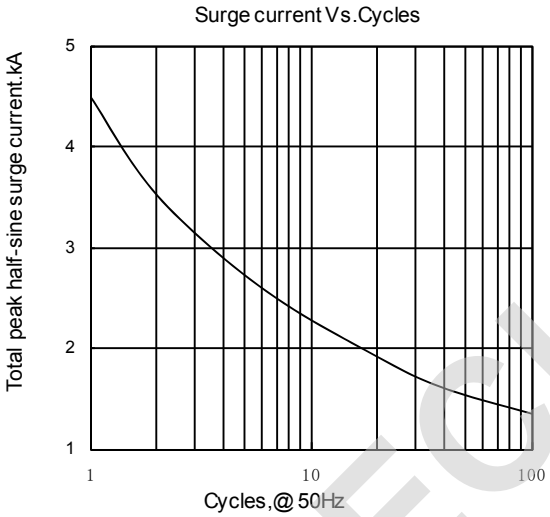


Fig3

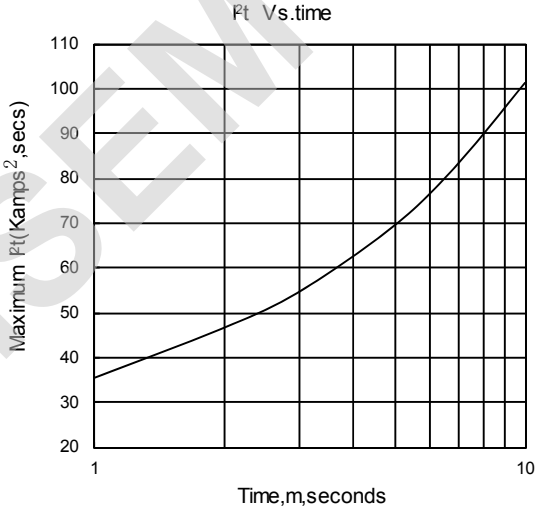


Fig4

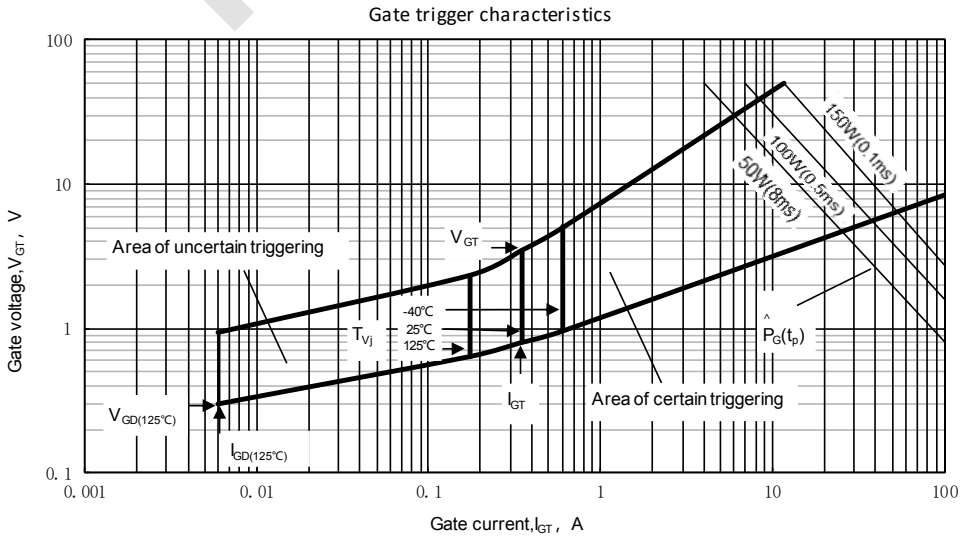
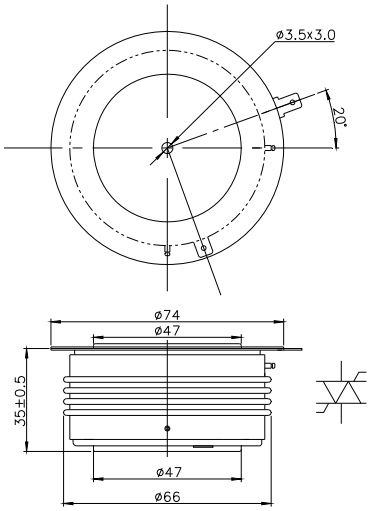


Fig.5

Outline:



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